PROCESS CP357X

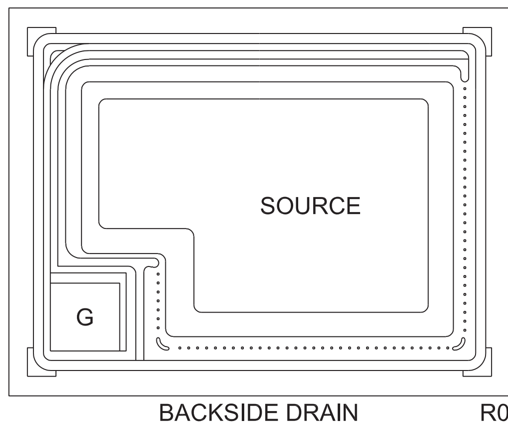
Small Signal MOSFET Transistor

N-Channel Enhancement-Mode MOSFET Chip

PROCESS DETAILS

Die Size	22 x 17 MILS
Die Thickness	5.9 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	14 x 9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R0

GROSS DIE PER 6 INCH WAFER
63,570

PRINCIPAL DEVICE TYPE
CMLDM3737

R0 (17-November 2010)

PROCESS CP357X

Typical Electrical Characteristics